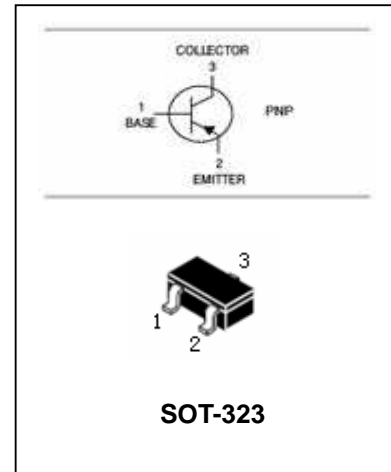


## PNP Silicon Epitaxial Planar Transistor

## 2SA1579W

### FEATURES

- Power dissipation.( $P_C=200\text{mW}$ )
- Excellent  $H_{FE}$  Linearity.



### APPLICATIONS

- General purpose application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1579W	HP/HQ/HR	SOT-323

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-50	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

**PNP Silicon Epitaxial Planar Transistor****2SA1579W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -100V, I_E = 0$			-0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-0.5	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -6V, I_C = -2mA$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.5	V
Transition frequency	$f_T$	$V_{CE} = -12V, I_C = -2mA$ $f = 30MHz$		140		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -12V, I_E = 0, f = 1MHz$		3.2		pF

**CLASSIFICATION OF  $h_{FE}$** 

Rank	S	R
Range	180-390	270-560
marking	RR	RS

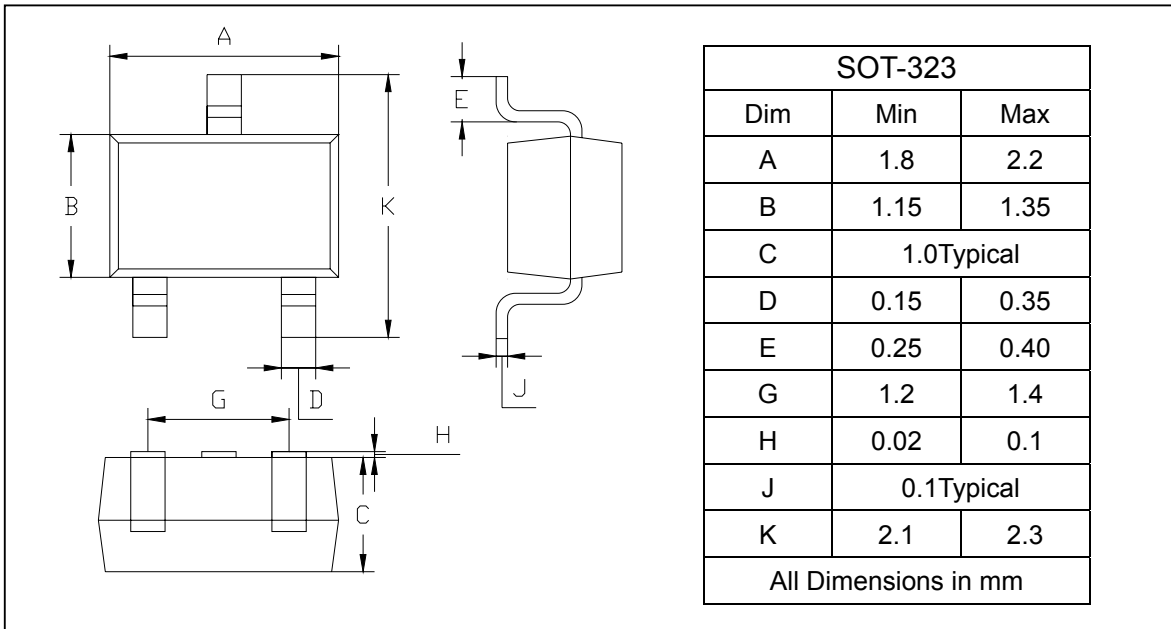
## PNP Silicon Epitaxial Planar Transistor

## 2SA1579W

### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### PACKAGE INFORMATION

Device	Package	Shipping
2SA1579W	SOT-323	3000/Tape&Reel